### 

## **30V P-Channel Enhancement Mode MOSFET**

Voltage

Current -50 A

DFN3333-8L

07

### Features

•  $R_{DS(ON)}$ ,  $V_{GS}$ @-10V, $I_D$ @-10A<8.5m $\Omega$ 

-30 V

- $R_{DS(ON)}$ ,  $V_{GS}$ @-4.5V, $I_D$ @-8A<14m $\Omega$
- High switching speed
- Improved dv/dt capability
- Low gate charge
- Low reverse transfer capacitance
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

### **Mechanical Data**

- Case: DFN3333-8L Package
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 0.001 ounces, 0.03 grams

## Maximum Ratings and Thermal Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V <sub>DS</sub>	-30	V	
Gate-Source Voltage		$V_{GS}$	<u>+</u> 20	V	
Continuous Drain Current	T <sub>C</sub> =25°C	I <sub>D</sub>	-50	A	
	T <sub>C</sub> =100°C		-32		
Pulsed Drain Current <sup>(Note 1)</sup>	Tc=25°C	I <sub>DM</sub>	-200		
Power Dissipation	T <sub>C</sub> =25°C	PD	60	14/	
	Tc=100°C		24	W	
Continuous Drain Current	T <sub>A</sub> =25°C	ID	-10	А	
	T <sub>A</sub> =70°C		-8	А	
Power Dissipation	T <sub>A</sub> =25°C	D	2.0	w	
Power Dissipation	T <sub>A</sub> =70°C	PD	1.3		
Operating Junction and Storage Temperature Range		$T_{J}, T_{STG}$	-55~150	٥C	
Typical Thermal Resistance <sup>(Note 4,5)</sup>	Junction to Case	Rejc	2.1	°C/W	
	Junction to Ambient	R <sub>0JA</sub>	62.5		

• Limited only By Maximum Junction Temperature



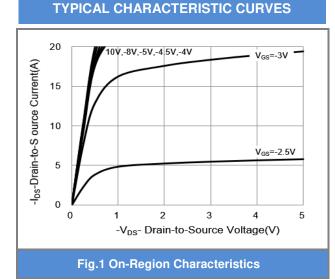
### Electrical Characteristics (TA=25°C unless otherwise noted)

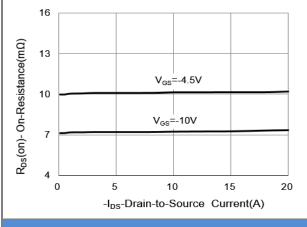
PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS			
Static									
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V,I <sub>D</sub> =-250uA	-30	-	-	V			
Gate Threshold Voltage	$V_{\text{GS(th)}}$	V <sub>DS</sub> =V <sub>GS</sub> ,I <sub>D</sub> =-250uA	-1.0	-1.5	-2.5	V			
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =-10V,I <sub>D</sub> =-10A	-	7.1	8.5	mΩ			
		V <sub>GS</sub> =-4.5V,I <sub>D</sub> =-8A	-	10	14				
Zero Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =-30V,V <sub>GS</sub> =0V	-	-	-1.0	uA			
Gate-Source Leakage Current	lgss	V <sub>GS</sub> = <u>+</u> 20V,V <sub>DS</sub> =0V	-	-	<u>+</u> 100	nA			
Dynamic <sup>(Note 6)</sup>									
Total Gate Charge	Qg	$V_{DS}$ =-15V, I <sub>D</sub> =-10A, $V_{GS}$ =-4.5V <sup>(Note 1,2)</sup>	-	27	-	nC			
Gate-Source Charge	Q <sub>gs</sub>		-	8.4	-				
Gate-Drain Charge	Q <sub>gd</sub>		-	8.7	-				
Input Capacitance	Ciss	V <sub>DS</sub> =-15V, V <sub>GS</sub> =0V,	-	3228	-	pF			
Output Capacitance	Coss		-	396	-				
Reverse Transfer Capacitance	Crss	f=1.0MHZ	-	254	-				
Turn-On Delay Time	td <sub>(on)</sub>		-	10	-	ns			
Turn-On Rise Time	tr	V <sub>DS</sub> =-15V,ID=-1A, V <sub>GS</sub> =-10V, R <sub>G</sub> =6Ω (Note 1,2)	-	13	-				
Turn-Off Delay Time	td <sub>(off)</sub>		-	111	-				
Turn-Off Fall Time	t <sub>f</sub>		-	51	-				
Drain-Source Diode									
Maximum Continuous Drain-Source			-	-	-50	А			
Diode Forward Current	Is								
Diode Forward Voltage	V <sub>SD</sub>	Is=-1A,V <sub>GS</sub> =0V	-	-0.7	-1	V			

NOTES :

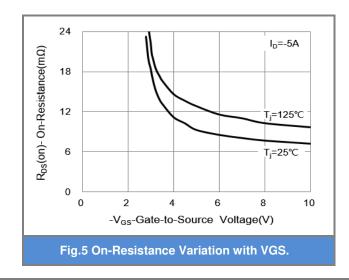
- 1. Pulse width</br>
- 2. Essentially independent of operating temperature typical characteristics
- Repetitive rating, pulse width limited by junction temperature T<sub>J(MAX)</sub>=150°C. Ratings are based on low frequency and duty cycles to keep initial T<sub>J</sub> =25°C.
- 4. The maximum current rating is package limited
- 5. R<sub>®JA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch<sup>2</sup> with 2oz.square pad of copper
- 6. Guaranteed by design, not subject to production testing.

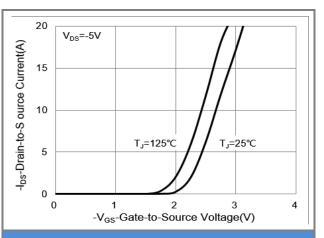




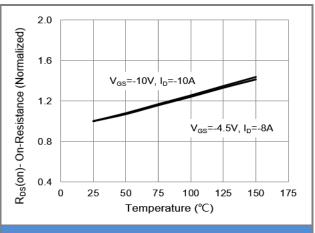


#### Fig.3 On-Resistance vs. Drain Current

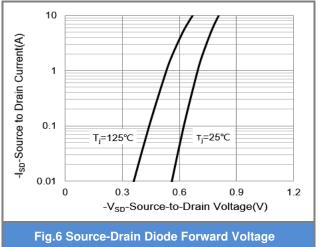




#### **Fig.2 Transfer Characteristics**



#### Fig.4 On-Resistance vs. Junction temperature





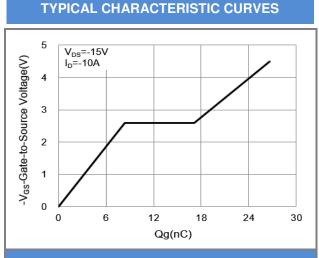


Fig.7 Gate-Charge Characteristics

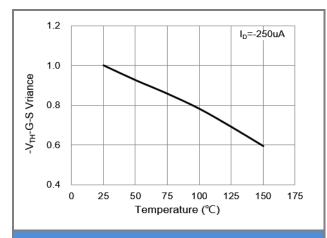
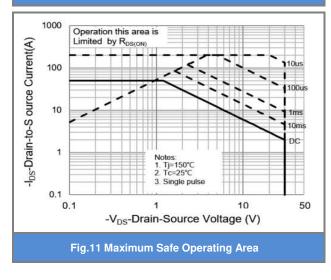
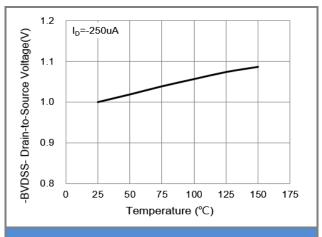


Fig.9 Threshold Voltage Variation with Temperature







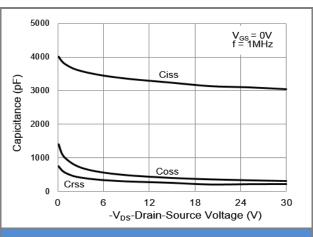
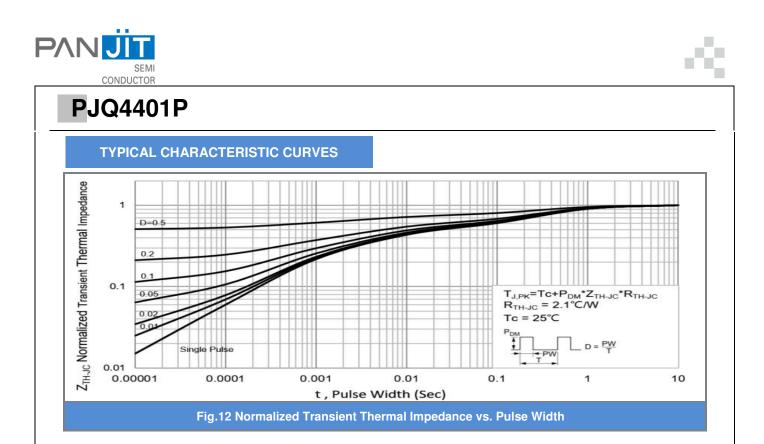


Fig.10 Capacitance vs. Drain-Source Voltage

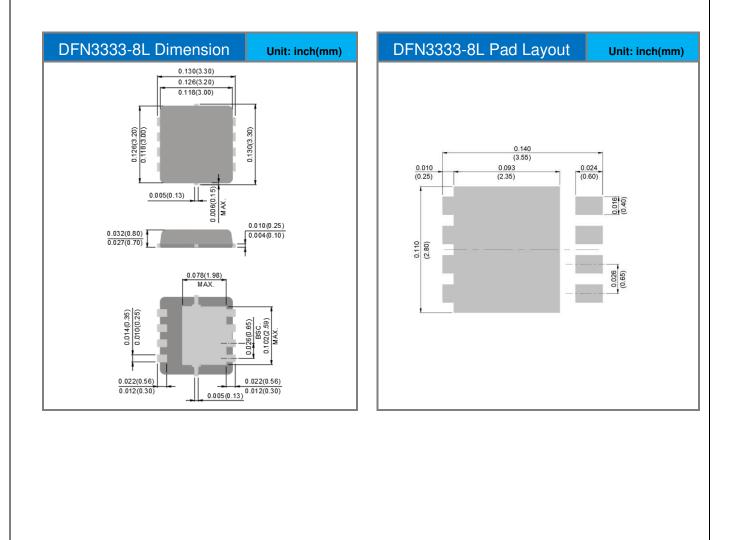




### Part No. Packing Code Version

Part No. Packing Code	Package Type	Packing Type	Marking	Version
PJQ4401P_R2_00001	DFN3333-8L	5K pcs / 13" reel	4401	Halogen free RoHS compliant

## **Packaging Information & Mounting Pad Layout**





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